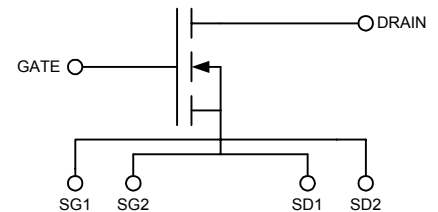
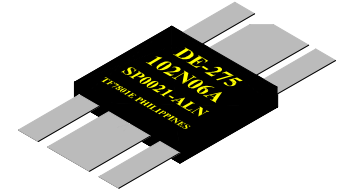


N-Channel Enhancement Mode  
Avalanche Rated  
Low  $Q_g$  and  $R_g$   
High  $dv/dt$   
Nanosecond Switching

Preliminary Data Sheet

$V_{DSS} = 1000 \text{ V}$   
 $I_{D25} = 6 \text{ A}$   
 $R_{DS(on)} = 2.0 \Omega$   
 $P_{DHS} = 375 \text{ W}$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1000	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	1000	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_c = 25^\circ\text{C}$	6	A
$I_{DM}$	$T_c = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	48	A
$I_{AR}$	$T_c = 25^\circ\text{C}$	6	A
$E_{AR}$	$T_c = 25^\circ\text{C}$	20	mJ
$dv/dt$	$I_s \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 0.2 \Omega$	5	V/ns
	$I_s = 0$	>200	V/ns
$P_{DHS}$	$T_c = 25^\circ\text{C}$ Derate $3.0 \text{ W}/^\circ\text{C}$ above $25^\circ\text{C}$	375	W
$P_{DAMB}$	$T_c = 25^\circ\text{C}$	3.0	W
$R_{thJHS}$		0.33	K/W
$T_J$		-55...+150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$T_L$	1.6mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
<b>Weight</b>		2	g



**Features**

- Isolated Substrate
  - high isolation voltage (>2500V)
  - excellent thermal transfer
  - Increased temperature and power cycling capability
- IXYS advanced low  $Q_g$  process
- Low gate charge and capacitances
  - easier to drive
  - faster switching
- Low  $R_{DS(on)}$
- Very low insertion inductance (<2nH)
- No beryllium oxide (BeO) or other hazardous materials

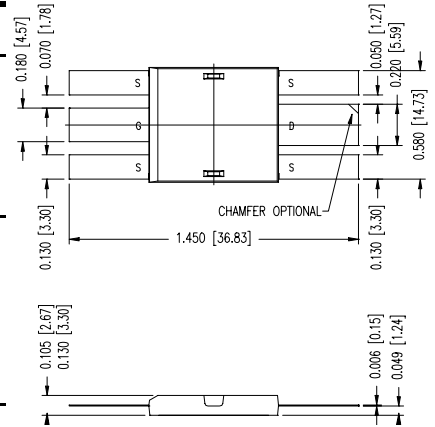
**Advantages**

- Optimized for RF and high speed switching at frequencies to 100MHz
- Easy to mount—no insulators needed
- High power density

Symbol	Test Conditions	Characteristic Values		
		$T_J = 25^\circ\text{C}$ unless otherwise specified		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 3 \text{ ma}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ ma}$	2.5		5.5 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0$ , $T_J = 125^\circ\text{C}$			50 $\mu\text{A}$
				1 mA
$R_{DS(on)}$	$V_{GS} = 15 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$			2.5 $\Omega$
$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 0.5 I_{D25}$ , pulse test	2	6	S

**Symbol Test Conditions Characteristic Values**  
( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
$R_G$			0.3	$\Omega$
$C_{iss}$			1800	pF
$C_{oss}$	$V_{GS} = 0\text{ V}, V_{DS} = 0.8 V_{DSS(max)},$ $f = 1\text{ MHz}$		100	pF
$C_{rss}$			30	pF
$T_{d(on)}$			3	ns
$T_{on}$	$V_{GS} = 15\text{ V}, V_{DS} = 0.8 V_{DSS}$ $I_D = 0.5 I_{DM}$		2	ns
$T_{d(off)}$	$R_G = 0.2\ \Omega$ (External)		4	ns
$T_{off}$			5	ns
$Q_{g(on)}$			50	nC
$Q_{gs}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}$ $I_D = 0.5 I_{D25}$		20	nC
$Q_{gd}$			30	nC



**Source-Drain Diode Characteristic Values**  
( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			6 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			48 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s},$ duty cycle $\leq 2\%$			1.5 V
$T_{rr}$			200	ns
$Q_{RM}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s},$ $V_R = 100\text{ V}$		0.6	$\mu\text{C}$
$I_{RM}$			4	A

Directed Energy, Inc. reserves the right to change limits, test conditions and dimensions.

DEI MOSFETS are covered by one or more of the following U.S. patents:

4,835,592	4,850,072	4,881,106	4,891,686	4,931,844	5,017,508
5,034,796	5,049,961	5,063,307	5,187,117	5,237,481	5,486,715
5,381,025	5,640,045				

102N06A DE-SERIES SPICE Model

The DE-SERIES SPICE Model is illustrated in Figure 1. The model is an expansion of the SPICE level 3 MOSFET model. It includes the stray inductive terms  $L_G$ ,  $L_S$  and  $L_D$ .  $R_d$  is the  $R_{DS(ON)}$  of the device,  $R_{ds}$  is the resistive leakage term. The output capacitance,  $C_{OSS}$ , and reverse transfer capacitance,  $C_{RSS}$  are modeled with reversed biased diodes. This provides a varactor type response necessary for a high power device model. The turn on delay and the turn off delay are adjusted via  $R_{on}$  and  $R_{off}$ .

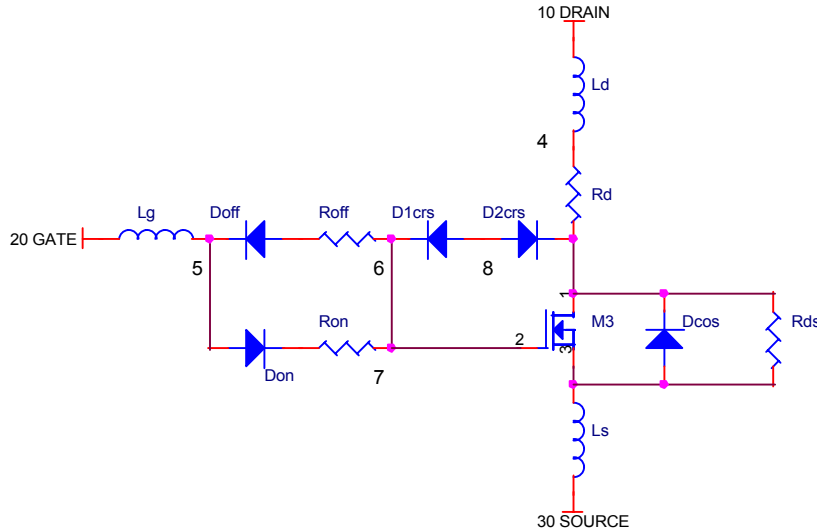


Figure 1 DE-SERIES SPICE Model

This SPICE model may be downloaded as a text file from the DEI web site at [www.directedenergy.com/spice.htm](http://www.directedenergy.com/spice.htm)

Net List:

```
*SYM=POWMOSN
.SUBCKT 102N06A 10 20 30
* TERMINALS: D G S
* 1000 Volt 6 Amp 2.0 Ohm N-Channel Power MOSFET
M1 1 2 3 3 DMOS L=1U W=1U
RON 5 6 .5
DON 6 2 D1
ROF 5 7 1.0
DOF 2 7 D1
D1CRS 2 8 D2
D2CRS 1 8 D2
CGS 2 3 1.9N
RD 4 1 1.7
DCOS 3 1 D3
RDS 1 3 5.0MEG
LS 3 30 .5N
LD 10 4 1N
LG 20 5 1N
.MODEL DMOS NMOS (LEVEL=3 VTO=4 KP=2.3)
.MODEL D1 D (IS=.5F CJO=10P BV=100 M=.5 VJ=.2 TT=1N)
.MODEL D2 D (IS=.5F CJO=400P BV=1000 M=.6 VJ=.6 TT=1N RS=10M)
.MODEL D3 D (IS=.5F CJO=400P BV=1000 M=.35 VJ=.6 TT=400N RS=10M)
.ENDS
```

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**Directed Energy, Inc.**  
An IXYS Company  
2401 Research Blvd., Suite 108  
Fort Collins, CO USA 80526  
970-493-1901 Fax: 970-493-1903  
Email: [deiinfo@directedenergy.com](mailto:deiinfo@directedenergy.com)  
Web: <http://www.directedenergy.com>